## MSKSEMI















**ESD** 

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# Broduct data sheet













**SOT - 23** 



- 2. EMITTER
- 3. COLLECTOR

TRANSISTOR (PNP)

#### **FEATURES**

High Breakdown Voltage

MARKING:4D

#### MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-Base Voltage	-400	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-400	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
Ic	Collector Current -Continuous	-200	mA
I <sub>CM</sub>	Collector Current -Pulsed	-300	mA
Pc	Collector Power Dissipation	350	mW
R <sub>OJA</sub>	Thermal Resistance From Junction To Ambient	357	°C/W
$T_J, T_stg$	Operation Junction and Storage Temperature Range	-55∼+150	ပူ

#### ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)

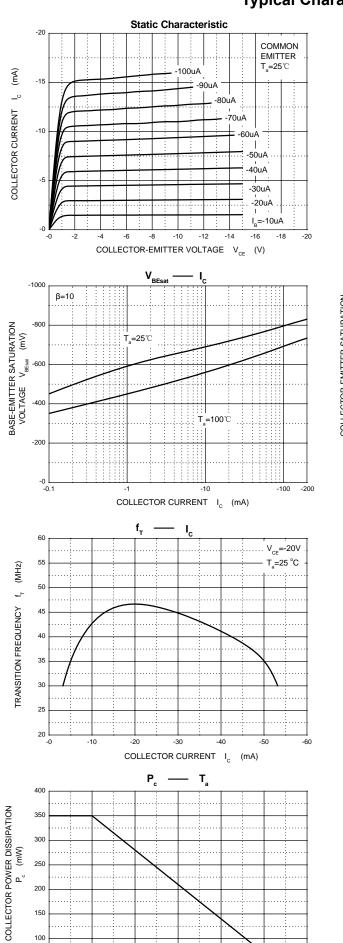
Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =-100μA, I <sub>E</sub> =0	-400			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =-1mA, I <sub>B</sub> =0	-400			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I <sub>E</sub> =-100μA, I <sub>C</sub> =0	-5			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =-400V, I <sub>E</sub> =0			-0.1	μA
Collector cut-off current	I <sub>CEO</sub>	V <sub>CE</sub> =-400V, I <sub>B</sub> =0			-5	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =-4V, I <sub>C</sub> =0			-0.1	μA
	h <sub>FE(1)</sub>	V <sub>CE</sub> =-10V, I <sub>C</sub> =-10mA	80		300	
DC current gain	h <sub>FE(2)</sub>	V <sub>CE</sub> =-10V, I <sub>C</sub> =-1mA	70			
De current gam	h <sub>FE(3)</sub>	V <sub>CE</sub> =-10V, I <sub>C</sub> =-100mA	40			
	h <sub>FE(4)</sub>	V <sub>CE</sub> =-10V, I <sub>C</sub> =-50mA	40			
Collector-emitter saturation voltage	V <sub>CE(sat)1</sub>	I <sub>C</sub> =-10mA, I <sub>B</sub> =-1mA			-0.2	V
Conector-enlitter Saturation voltage	V <sub>CE(sat)2</sub>	I <sub>C</sub> =-50mA, I <sub>B</sub> =-5mA			-0.3	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =-10mA, I <sub>B</sub> =-1mA			-0.75	V
Transition fraguency	f⊤	V <sub>CE</sub> =-20V,I <sub>C</sub> =-10mA,	50			MHz
Transition frequency	IŢ	f=30MHz	50			IVII



Semiconductor

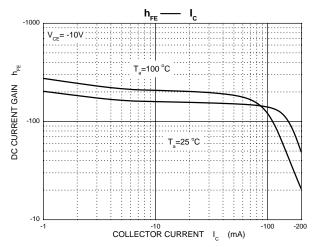
#### Compiance

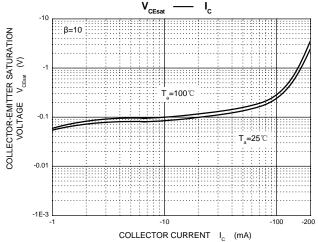
#### **Typical Characteristics**

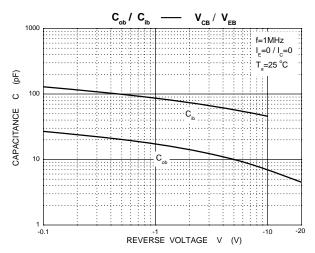


50 75 100

AMBIENT TEMPERATURE T<sub>a</sub> (°C)





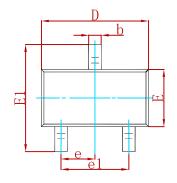


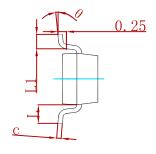


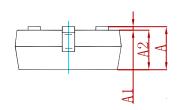
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#### **PACKAGE MECHANICAL DATA**

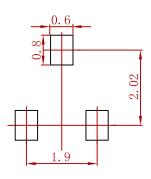






Cumhal	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.037	7 TYP	
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

### **Suggested Pad Layout**



- 1.Controlling dimension:in millimeters.2.General tolerance:± 0.05mm.3.The pad layout is for reference purposes only.

#### **REEL SPECIFICATION**

P/N	PKG	QTY
MMBTA94-MS	SOT-23	3000



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